

**Description**

The SX2P15LI uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 10V. This device is suitable for use as a Battery protection or in other Switching application.

**General Features**

$V_{DS} = -150V$   $I_D = -2.7A$

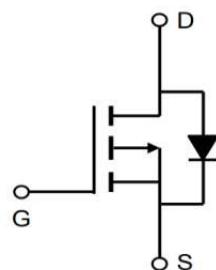
$R_{DS(ON)} < 780m\Omega$  @  $V_{GS}=10V$

**Application**

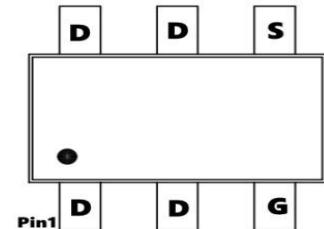
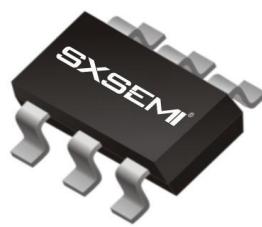
Brushless motor

Load switch

Uninterruptible power supply



SOT-23-6L

**Absolute Maximum Ratings ( $T_c=25^\circ C$  unless otherwise noted)**

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	-150	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D@T_A=25^\circ C$	Continuous Drain Current, $-V_{GS} @ -10V^1$	-2.7	A
$I_D@T_A=70^\circ C$	Continuous Drain Current, $-V_{GS} @ -10V^1$	-1.8	A
$I_{DM}$	Pulsed Drain Current <sup>2</sup>	-8.5	A
$E_{AS}$	Single Pulse Avalanche Energy <sup>3</sup>	56.5	mJ
$I_{AS}$	Avalanche Current	5	A
$P_D@T_A=25^\circ C$	Total Power Dissipation <sup>4</sup>	2	W
$T_{STG}$	Storage Temperature Range	-55 to 150	°C
$T_J$	Operating Junction Temperature Range	-55 to 150	°C
$R_{\theta JA}$	Thermal Resistance Junction-Ambient <sup>1</sup>	125	°C/W
$R_{\theta JC}$	Thermal Resistance Junction-Case <sup>1</sup>	40	°C/W

**P-Channel Electrical Characteristics (TJ =25 °C, unless otherwise noted)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BVDSS	Drain-Source Breakdown Voltage	VGS=0V , ID=-250uA	-150	-168	---	V
RDS(ON)	Static Drain-Source On-Resistance	VGS=-10V , ID=1A	---	620	780	mΩ
RDS(ON)	Static Drain-Source On-Resistance	VGS=-6V , ID=-0.5A	---	700	980	
VGS(th)	Gate Threshold Voltage	VGS=VDS , ID =-250uA	-2.0	-3.0	-4.0	V
IDSS	Drain-Source Leakage Current	VDS=120V ,VGS=0V ,TJ=25°C	---	---	1	uA
IDSS	Drain-Source Leakage Current	VDS=120V ,VGS=0V ,TJ=85°C	---	---	30	uA
IGSS	Gate-Source Leakage Current	VGS=±20V , VDS=0V	---	---	±100	nA
Rg	Gate Resistance	VDS=0V , VGS=0V , f=1MHz	---	12	---	Ω
Qg	Total Gate Charge	VDS=-75V , VGS=-10V , ID=-1A	---	10.8	---	nC
Qgs	Gate-Source Charge		---	3.1	---	nC
Qgd	Gate-Drain Charge		---	2.2	---	nC
Td(on)	Turn-On Delay Time	VDD=-30V , VGS=-10V , RG=6Ω, ID=1A	---	21	---	ns
Tr	Rise Time		---	16	---	ns
Td(off)	Turn-Off Delay Time		---	40	---	ns
Tf	Fall Time		---	18	---	ns
Ciss	Input Capacitance	VDS=-75V , VGS=0V , f=1MHz	---	706	---	pF
Coss	Output Capacitance		---	23	---	pF
Crss	Reverse Transfer Capacitance		---	13	---	pF

Note :

- 1、The data tested by surface mounted on a 1 inch 2 FR-4 board with 2OZ copper.
- 2、The data tested by pulsed , pulse width  $\leq$  300us , duty cycle  $\leq$  2%
- 3、The power dissipation is limited by 150°C junction temperature
- 4、The data is theoretically the same as ID and IDM , in real applications , should be limited by total power dissipation.

## Typical Characteristics

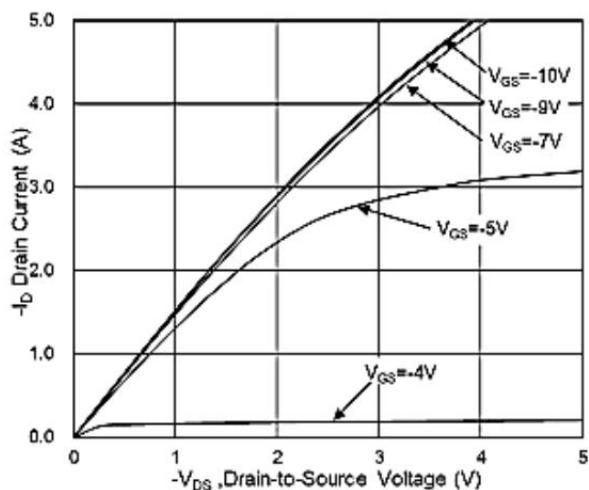


Fig.1 Typical Output Characteristics

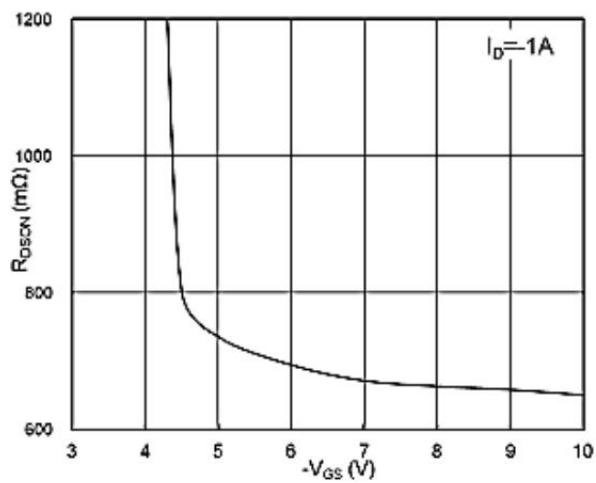


Fig.2 On-Resistance vs G-S Voltage

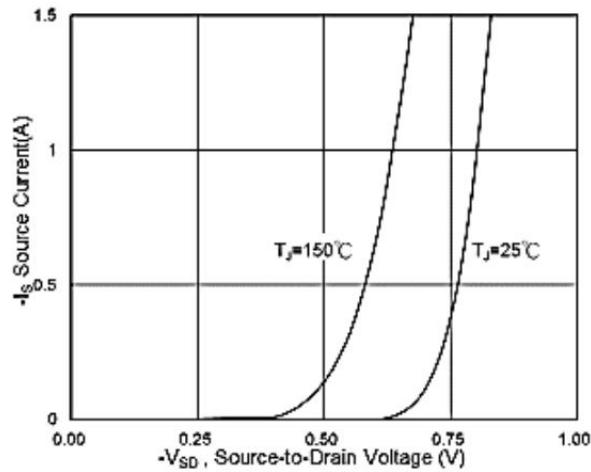


Fig.3 Source Drain Forward Characteristics

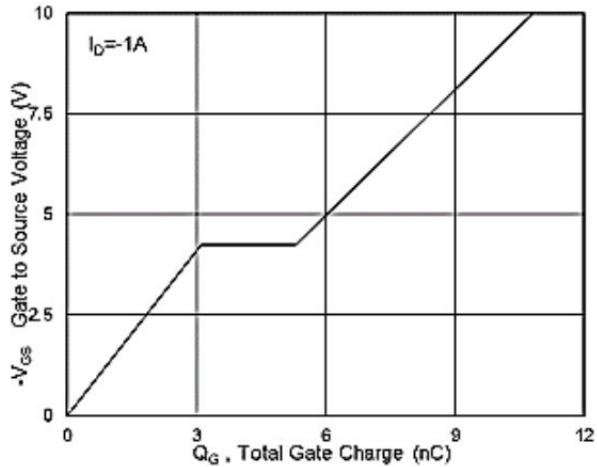


Fig.4 Gate-Charge Characteristics

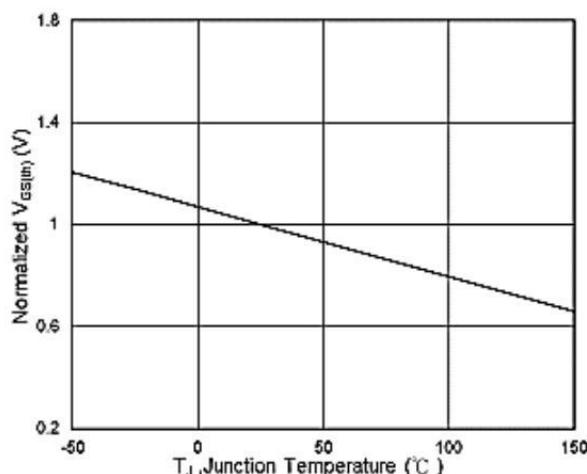


Fig.5 Normalized  $V_{GS(th)}$  vs  $T_J$

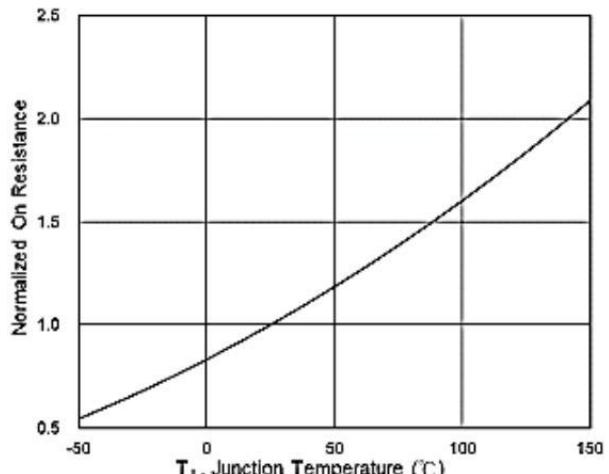
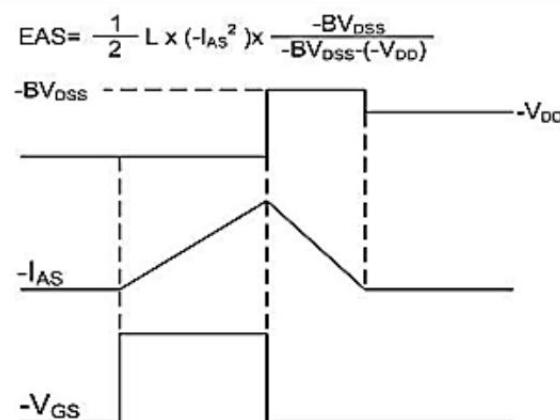
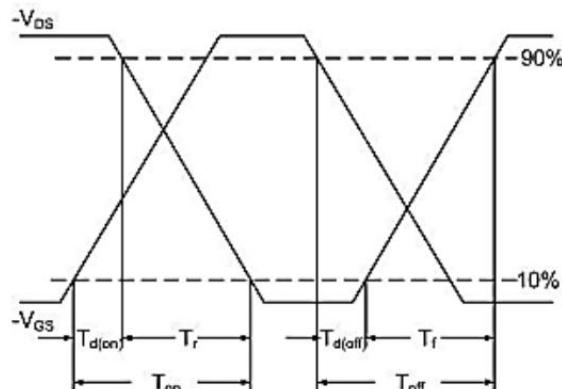
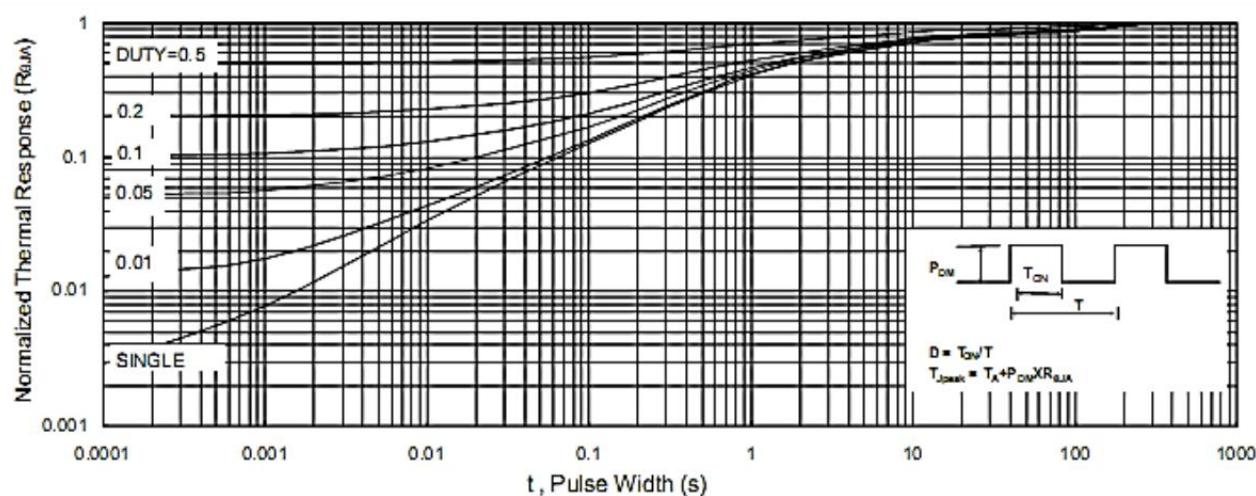
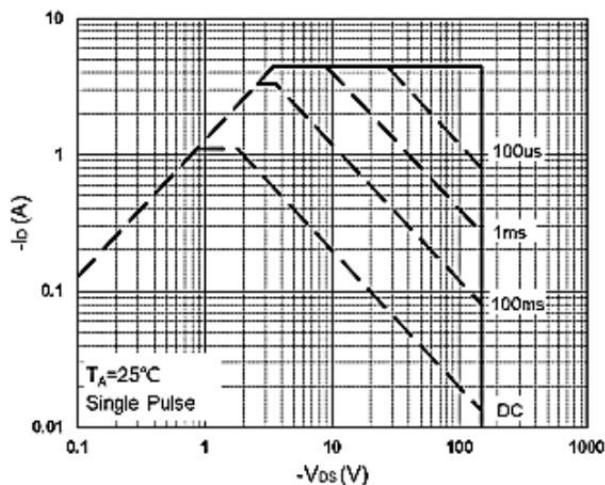
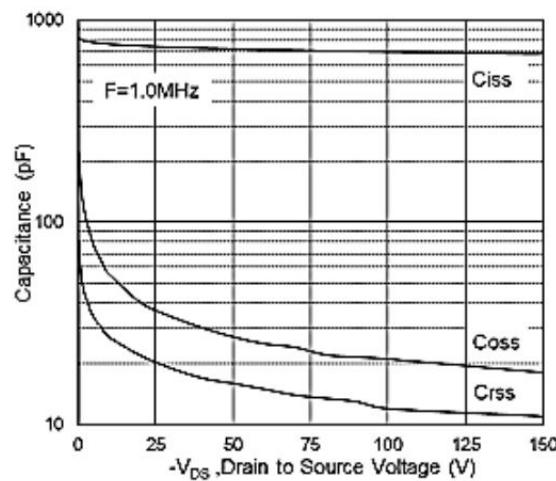
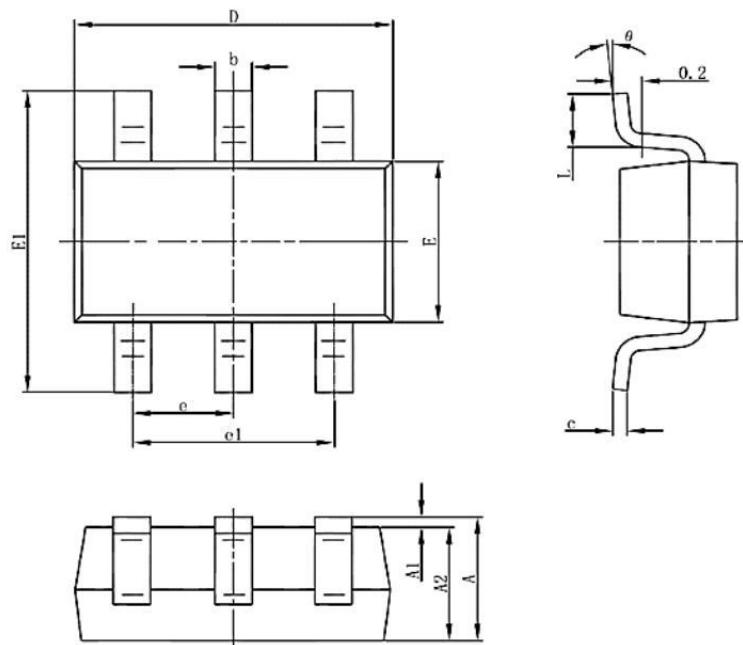


Fig.6 Normalized  $R_{DS(on)}$  vs  $T_J$

## Typical Characteristics



## Package Mechanical Data-SOT23-6-Single



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
C	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E	1.500	1.700	0.059	0.067
E1	2.650	2.950	0.104	0.116
e	0.950 (BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0	8	0	8

### Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
TAPING	SOT23-6L		3000